



REPLACEMENT SPECIFICATION PARAGRAPHS

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On Page 7, please delete lines 24-30 and replace them with
the following:

BI
Conventionally, the bias sputtering method has been utilized as a thin film formation process (metallization) for forming electrodes and wiring in LSI. For example, as shown in Fig. 5, it is utilized for embedding metal film wiring 10 in a dielectric 9 to flatten an upper surface, or, as shown in Fig. 4, for filling up a space between two wires 10 not to produce a hollow portion. On the other hand, it is entirely novel technique to employ bias sputtering or sputter etching for shaping the film described below.

On Page 28, line 24 please delete the following paragraph:

While this invention has been described as having a preferred design, the present invention can be further modified within the spirit and scope of this disclosure. This application is therefore intended to cover any variations, uses, or adaptations of the invention using its general principles. Further, this application is intended to cover such departures from the present disclosure as come within known or customary practice in the art to which this invention pertains and which fall within the limits of the appended claims.